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University Collage of Women for
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Structural, Optical and Electrical Properties of Diluted Magnetic Semiconductors "$Cd_{1-x}Mn_xSe$" Films.

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STRUCTURE, OPTICAL AND ELECTRICAL PROPERTIES OF DILUTED MAGNETIC SEMICONDUCTORS〝$Cd_{1-x}Mn_xSe$〞 FILMS.

THESIS SUBMITTED
FOR THE PH.D DEGREE IN PHYSICS (SOLID STATE)

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